

RIE Etcher Series

Uni-body Design Concept

Foot-print outstanding (ref 1.0m*1.0m)

Uniform Chamber Center Pump-down

Better process performance

Showerhead Gas Feed-in

Tuned as a preset parameter dependently

Configurable Plasma Discharge Gap

Tuned as a preset parameter dependently

Cost or Performance Orientation

RF, Pump, Values etc. depending on requirements

Sample Handling Options

Open-Load or Load-Lock



Specification	Parameters
Wafer Size Range	4,6,8,12 inch or multi-wafers optional
Etching Materials	Si-Based (Si/SiO ₂ /SiN _x /SiC/Quartz etc.), Compounds (InP/GaN/GaAs/Ga ₂ O ₃ /ZnS etc.), 1D&2D Materials (MoS ₂ /BN/Graphene etc.), Metals (Au/Pt/W/Ta/Mo etc.), Failure Analysis, etc.
Vacuum	TMP&Mechanical Pump
RF Power	Full Range 300-1000W, optional
Gas System	4 lines(Standard) or customized
Wafer Cooling	Water Cooling or He Backside Cooling optional
Wafer Stage Temperature Range	From -70°C to 200°C, optional
Non-Uniformity	Less than ±5% (Edge Exclusion)